

MA999

Silicon epitaxial planer type

For switching circuits

■ Features

- MA704A and MA151K chip with two elements incorporated
- Short reverse recovery period t_{rr}
- Automatic mounting possible

■ Absolute Maximum Ratings (Ta= 25°C)

● Unit-1(MA704A)

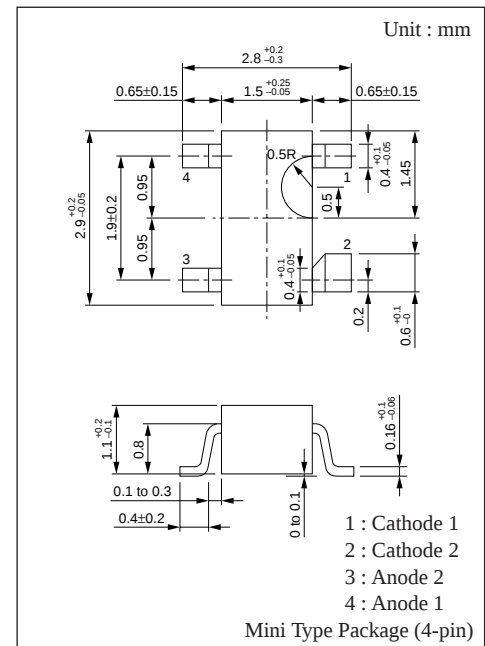
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Peak reverse voltage	V_{RM}	30	V
Forward current (DC)	I_F	30	mA
Peak forward current	I_{FM}	150	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	- 55 to + 125	°C

● Unit-2(MA151K)

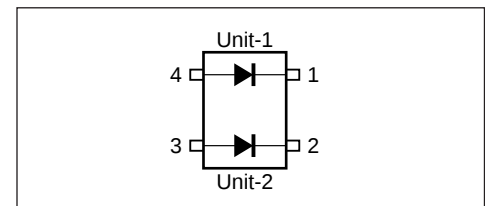
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	40	V
Forward current (DC)	I_F	100	mA
Peak forward current	I_{FM}	225	mA
Non-repetitive peak forward surge current	I_{FSM}^*	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	- 55 to +125	°C

* $t=1s$

■ Marking



■ Internal Connection



■ Electrical Characteristics (Ta= 25°C)

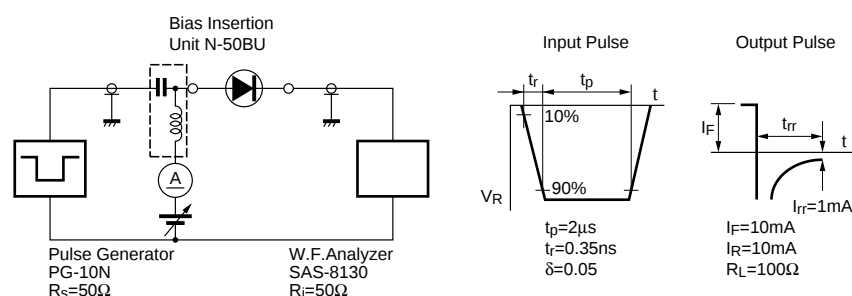
● Unit-1

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 30V$			300	nA
Forward voltage (DC)	V_{F1}	$I_F = 1mA$			0.4	V
	V_{F2}	$I_F = 30mA$			1.0	V
Terminal capacitance	C_t	$V_R = 1V, f = 1MHz$		1.5		pF
Reverse recovery time	t_{rr}^*	$I_F = I_R = 10mA$ $I_{rr} = 1mA, R_L = 100\Omega$		1.0		ns
Detection efficiency	η	$V_{in} = 3V_{(peak)}, f = 30MHz$ $R_L = 3.9k\Omega, C_L = 10pF$		65		%

Note 1 : Rated input/output frequency : 2000MHz

2 : This Schotky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention to the electric charge of a human body or the leakage from the equipment in use.

3 : * t_{rr} measuring circuit

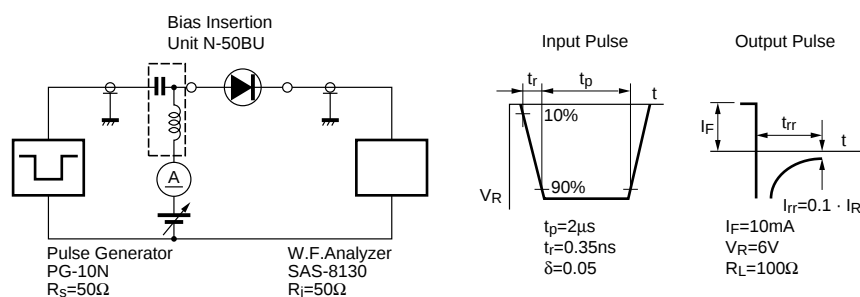


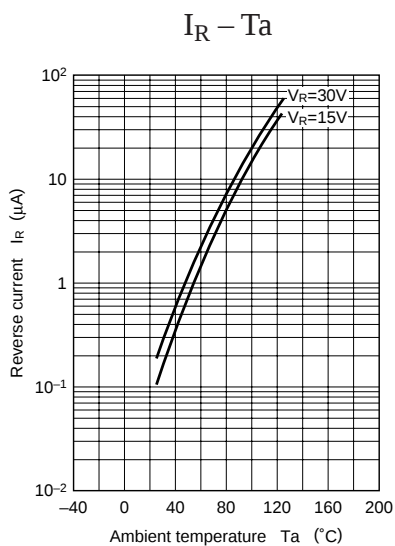
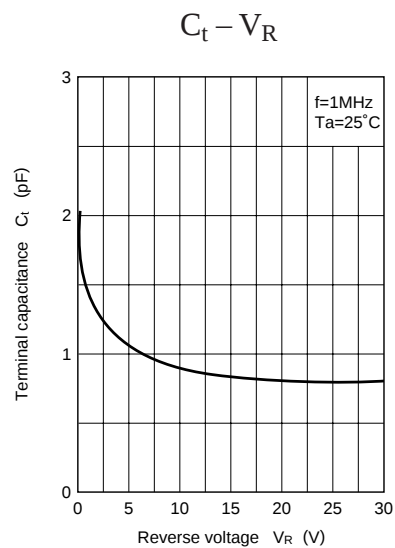
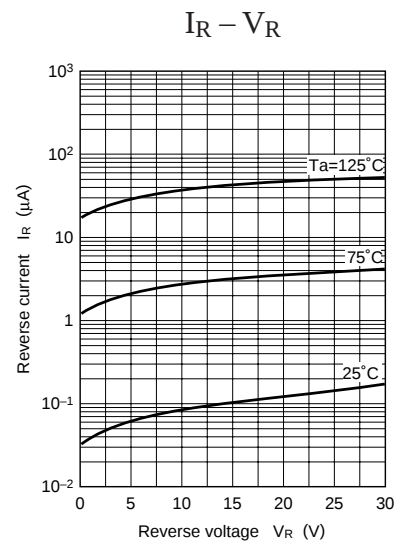
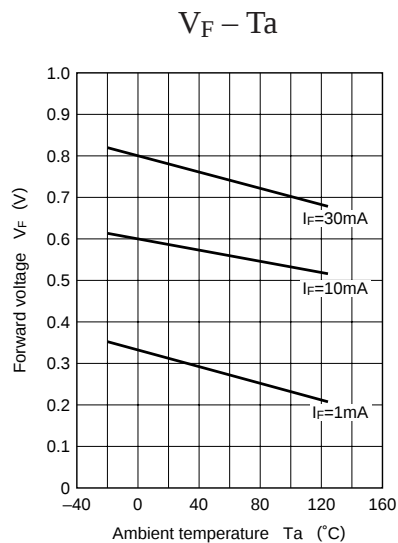
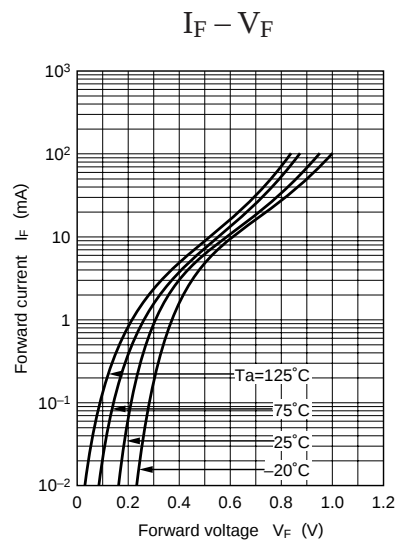
● Unit-2

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 35V$			100	nA
Forward voltage (DC)	V_F	$I_F = 100mA$		0.95	1.2	V
Reverse voltage (DC)	V_R	$I_R = 100\mu A$	40			V
Terminal capacitance	C_t	$V_R = 0V, f = 1MHz$		0.9	2	pF
Reverse recovery time	t_{rr}^*	$I_F = 10mA, V_R = 6V$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$			3	ns

Note 1 : Rated input/output frequency : 100MHz

2 : * t_{rr} measuring circuit



Characteristics chart of Unit-1(MA704A) (Between pins 1 and 4)


Characteristics chart of Unit-2(MA151K) (Between pins 2 and 3)